

Application No.: 10/788,913
Response dated: October 11, 2005
Reply to Office action dated: July 12, 1005

Amendments to the Specification:

Please replace the paragraph beginning at page 28, line 1, with the following amended paragraph:

~~Disclosed herein is an~~ An SRAM-compatible memory device performing performs a refresh operation ~~having with~~ separate fetching and rewriting operation periods. ~~and a method of driving the SRAM-compatible memory device. The SRAM-compatible memory device can be activated by a method of driving the SRAM-compatible memory device.~~ During a first refresh period, the SRAM-compatible memory device performs an operation of fetching data from a DRAM cell to be refreshed. During a second refresh period, the SRAM-compatible memory device performs an operation of rewriting the data fetched during the first refresh period in the refreshed DRAM cell. Accordingly, the length of an assigned refresh period is reduced, and the length of an entire external access period is also reduced.